

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph at page 3, beginning line 10 and ending on line 23, with the following:

According to an aspect of the present invention, there is provided a semiconductor device having a MOSFET, the MOSFET comprising source and drain regions formed in a major surface region of a semiconductor substrate, a gate insulating film formed on a channel region between the source and drain regions, a gate electrode which is formed on the gate insulating film and ~~includes~~ formed of a poly-Si_{1-x}Ge_x layer having a Ge/(Si+Ge) composition ratio x ($0 < x < 0.2$), a first metal silicide film which is formed on the gate electrode and essentially consists of NiSi_{1-y}Ge_y, and second and third metal silicide films which are formed on the source and drain regions, respectively, and essentially consist of NiSi.

Please delete the paragraph beginning at page 3, line 24 and ending at page 4, line 9.